

# MOSFET – Power, P-Channel, High Side Load Switch with Level-Shift, SC-88

8 V, ±1.3 A

## NTJD1155L

The NTJD1155L integrates a P and N-Channel MOSFET in a single package. This device is particularly suited for portable electronic equipment where low control signals, low battery voltages and high load currents are needed. The P-Channel device is specifically designed as a load switch using onsemi state-of-the-art trench technology. The N-Channel, with an external resistor (R1), functions as a level-shift to drive the P-Channel. The N-Channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The NTJD1155L operates on supply lines from 1.8 to 8.0 V and can drive loads up to 1.3 A with 8.0 V applied to both  $V_{IN}$  and  $V_{ON/OFF}$ .

### Features

- Extremely Low  $R_{DS(on)}$  P-Channel Load Switch MOSFET
- Level Shift MOSFET is ESD Protected
- Low Profile, Small Footprint Package
- $V_{IN}$  Range 1.8 to 8.0 V
- ON/OFF Range 1.5 to 8.0 V
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Rating		Symbol	Value	Unit
Input Voltage ( $V_{DSS}$ , P-Ch)		$V_{IN}$	8.0	V
ON/OFF Voltage ( $V_{GS}$ , N-Ch)		$V_{ON/OFF}$	8.0	V
Continuous Load Current (Note 1)	Steady State	$T_A = 25\text{ }^\circ\text{C}$	$I_L$	±1.3
		$T_A = 85\text{ }^\circ\text{C}$		±0.9
Power Dissipation (Note 1)	Steady State	$T_A = 25\text{ }^\circ\text{C}$	$P_D$	0.40
		$T_A = 85\text{ }^\circ\text{C}$		0.20
Pulsed Load Current	$t_p = 10\text{ }\mu\text{s}$	$I_{LM}$	±3.9	A
Operating Junction and Storage Temperature		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode)		$I_S$	-0.4	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

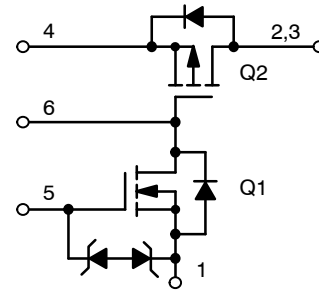
Characteristic	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	320	$^\circ\text{C}/\text{W}$
Junction-to-Foot – Steady State (Note 1)	$R_{\theta JF}$	220	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 inch sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

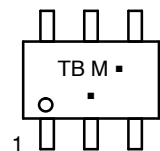
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	$I_D$ MAX
8.0 V	130 m $\Omega$ @ -4.5 V	±1.3 A
	170 m $\Omega$ @ -2.5 V	
	260 m $\Omega$ @ -1.8 V	

### SIMPLIFIED SCHEMATIC



SC-88  
(SOT-363)  
CASE 419B-02  
STYLE 30

### MARKING DIAGRAM



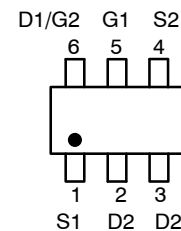
TB = Device Code

M = Date Code

▪ = Pb-Free Package

(Note: Microdot may be in either location)

### PIN ASSIGNMENT



### ORDERING INFORMATION

Device	Package	Shipping†
NTJD1155LT1G, NTJD1155LT2G	SC-88 (Pb-Free)	3000/Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

# NTJD1155L

## ELECTRICAL CHARACTERISTICS ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Q2 Drain-to-Source Breakdown Voltage	$V_{IN}$	$V_{GS2} = 0\text{ V}, I_{D2} = 250\text{ }\mu\text{A}$	-8.0			V
Forward Leakage Current	$I_{FL}$	$V_{GS1} = 0\text{ V}, V_{DS2} = -8.0\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$		1.0	$\mu\text{A}$
			$T_J = 125\text{ }^\circ\text{C}$		10	
Q1 Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS1} = 0\text{ V}, V_{GS1} = \pm 8.0\text{ V}$			$\pm 100$	nA
Q1 Diode Forward On-Voltage	$V_{SD}$	$I_S = -0.4\text{ A}, V_{GS1} = 0\text{ V}$		-0.8	-1.1	V

## ON CHARACTERISTICS

ON/OFF Voltage	$V_{ON/OFF}$		1.5		8.0	V	
Q1 Gate Threshold Voltage	$V_{GS1(th)}$	$V_{GS1} = V_{DS1}, I_D = 250\text{ }\mu\text{A}$	0.4		1.0	V	
Input Voltage	$V_{IN}$	$V_{GS1} = V_{DS1}, I_D = 250\text{ }\mu\text{A}$	1.8		8.0	V	
Q2 Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{ON/OFF} = 1.5\text{ V}$	$V_{IN} = 4.5\text{ V}, I_L = 1.2\text{ A}$		130	175	$\text{m}\Omega$
			$V_{IN} = 2.5\text{ V}, I_L = 1.0\text{ A}$		170	220	
			$V_{IN} = 1.8\text{ V}, I_L = 0.7\text{ A}$		260	320	
Load Current	$I_L$	$V_{DROP} \leq 0.2\text{ V}, V_{IN} = 5.0\text{ V}, V_{ON/OFF} = 1.5\text{ V}$	1.0			A	
		$V_{DROP} \leq 0.3\text{ V}, V_{IN} = 2.5\text{ V}, V_{ON/OFF} = 1.5\text{ V}$	1.0				

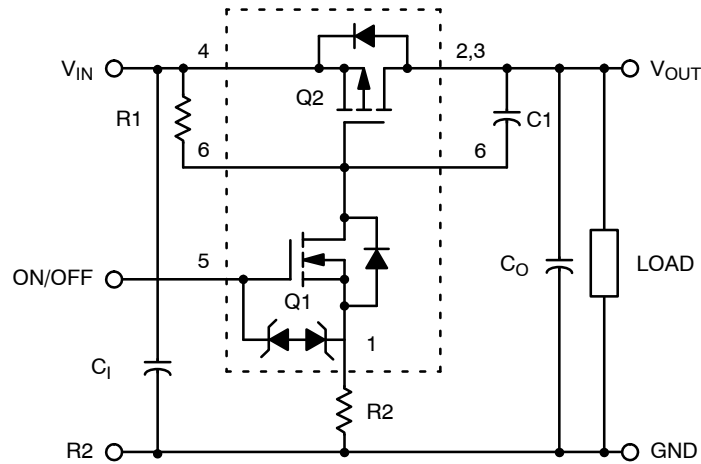


Figure 1. Load Switch Application

Components	Description	Values
R1	Pullup Resistor	Typical 10 k $\Omega$ to 1.0 M $\Omega$ *
R2	Optional Slew-Rate Control	Typical 0 to 100 k $\Omega$ *
$C_0, C_1$	Output Capacitance	Usually < 1.0 $\mu\text{F}$
C1	Optional In-Rush Current Control	Typical $\leq 1000\text{ pF}$

\* Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

# NTJD1155L

## TYPICAL PERFORMANCE CURVES ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)

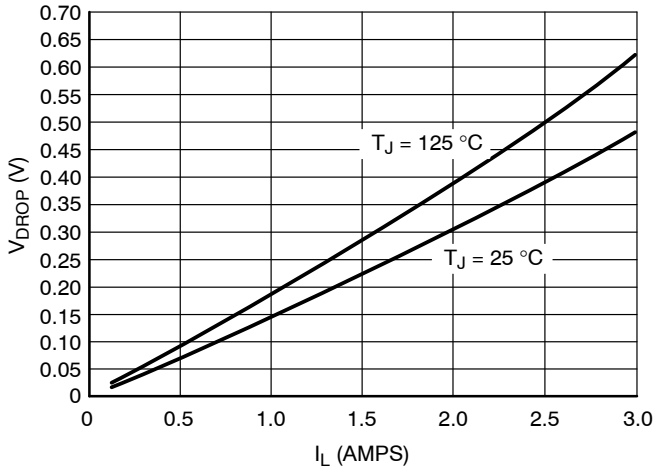


Figure 2.  $V_{drop}$  vs.  $I_L$  @  $V_{in} = 2.5\text{ V}$

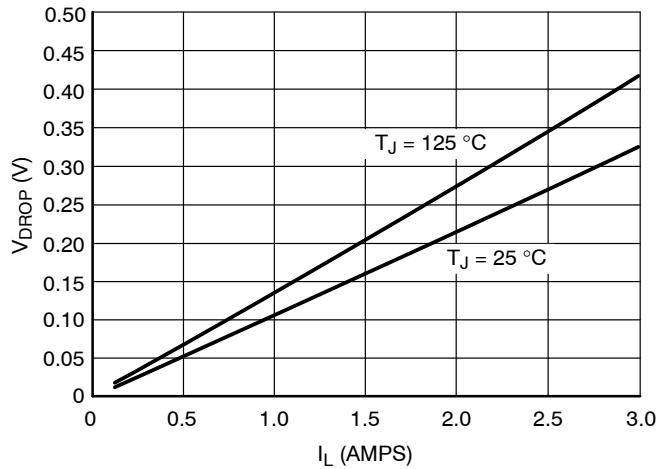


Figure 3.  $V_{drop}$  vs.  $I_L$  @  $V_{in} = 4.5\text{ V}$

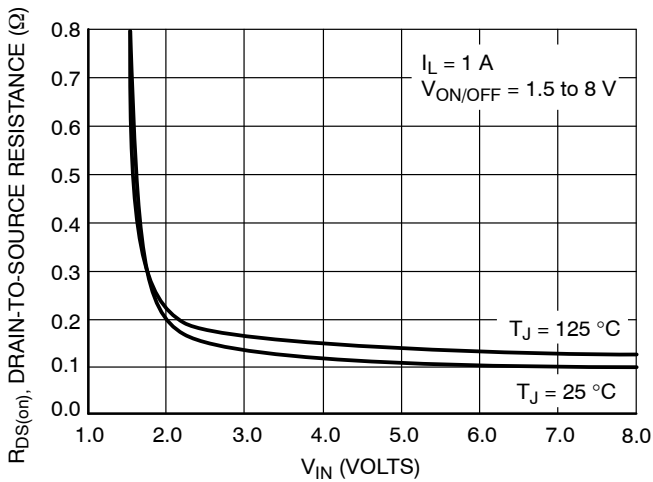


Figure 4. On-Resistance vs. Input Voltage

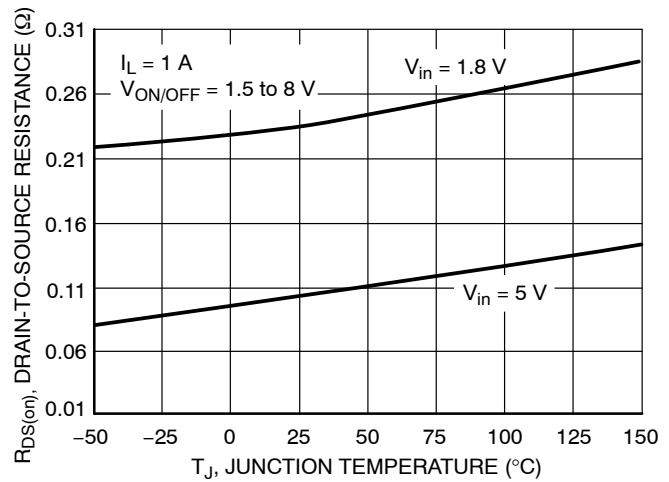


Figure 5. On-Resistance Variation with Temperature

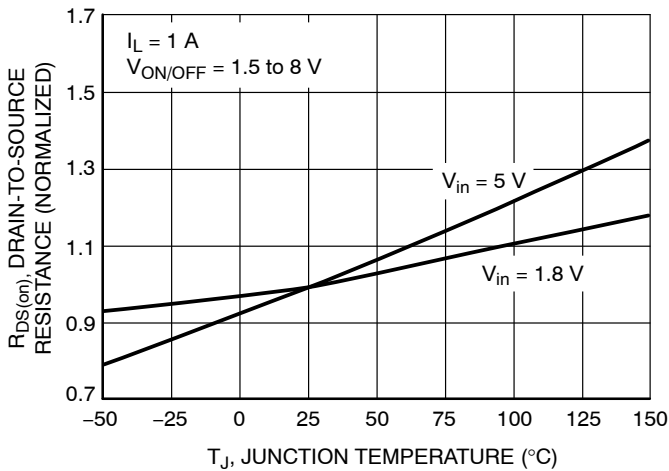


Figure 6. Normalized On-Resistance Variation with Temperature

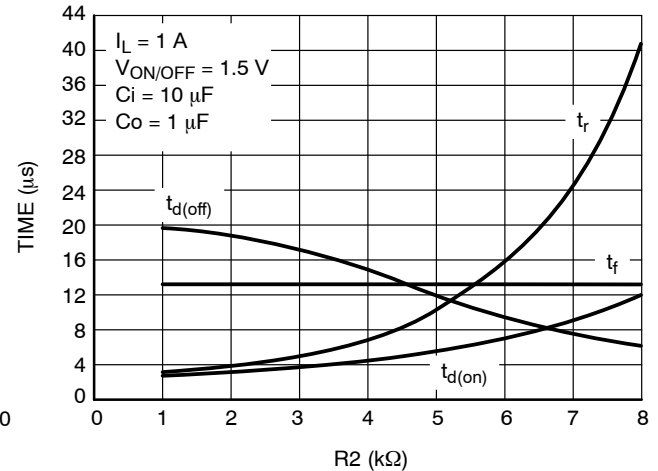
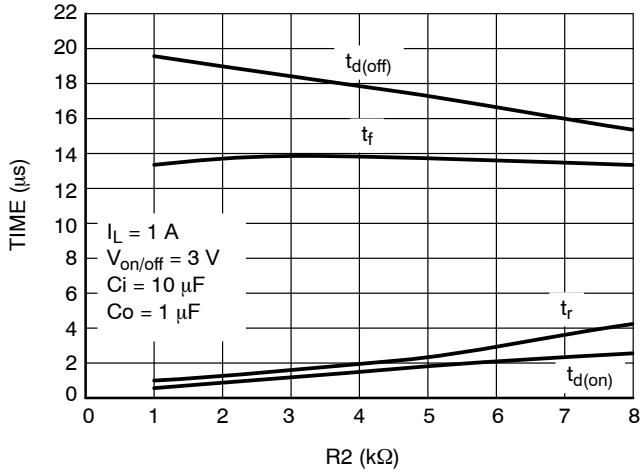


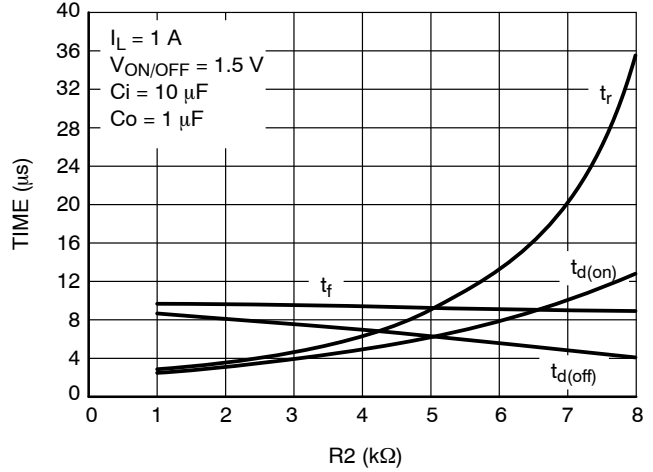
Figure 7. Switching Variation  $R2$  @  $V_{in} = 4.5\text{ V}$ ,  $R1 = 20\text{ k}\Omega$

# NTJD1155L

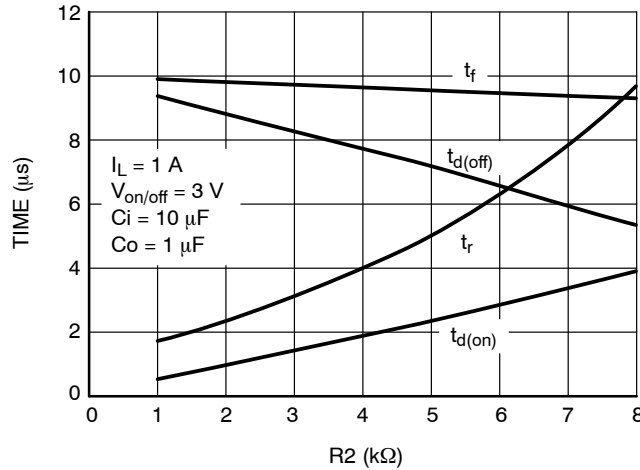
## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)



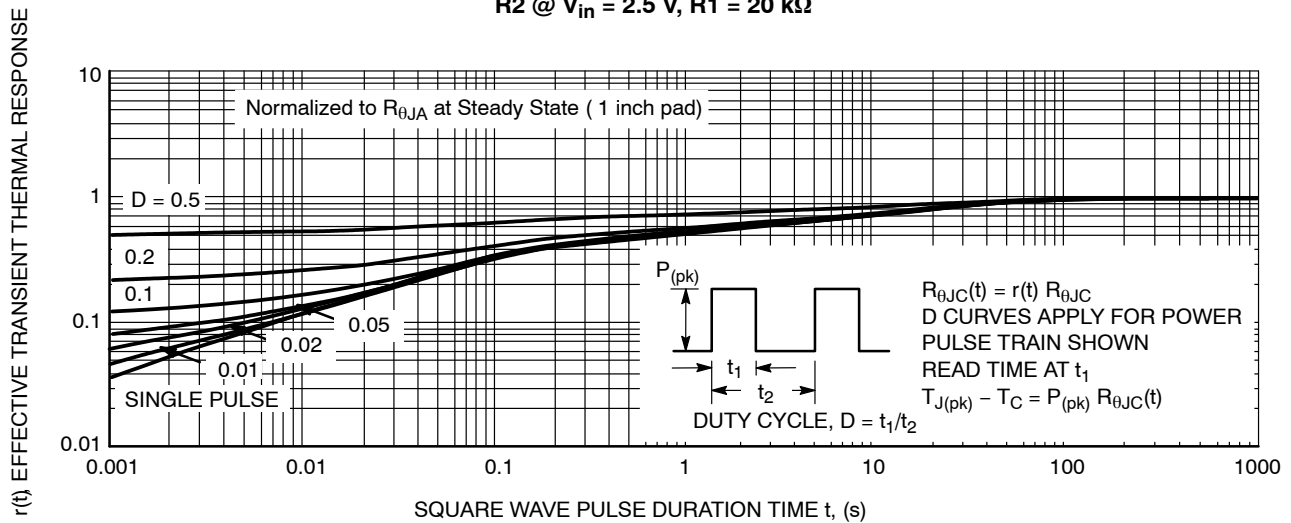
**Figure 8. Switching Variation**  
R2 @  $V_{in} = 4.5\text{ V}$ ,  $R_1 = 20\text{ k}\Omega$



**Figure 9. Switching Variation**  
R2 @  $V_{in} = 2.5\text{ V}$ ,  $R_1 = 20\text{ k}\Omega$



**Figure 10. Switching Variation**  
R2 @  $V_{in} = 2.5\text{ V}$ ,  $R_1 = 20\text{ k}\Omega$



**Figure 11. FET Thermal Response**

**REVISION HISTORY**

Revision	Description of Changes	Date
7	Document rebranded to <b>onsemi</b> format.	10/16/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

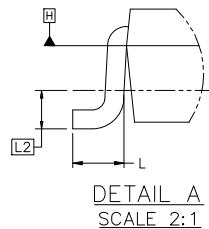
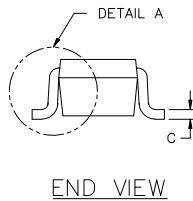
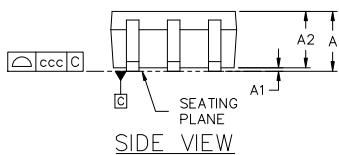
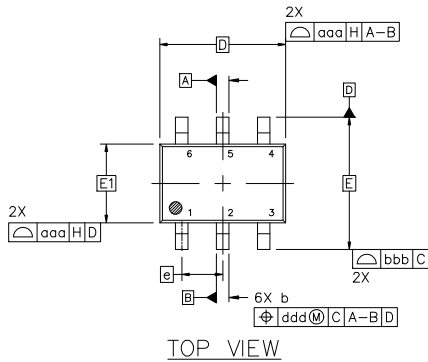


SC-88 2.00x1.25x0.90, 0.65P  
CASE 419B-02  
ISSUE Z

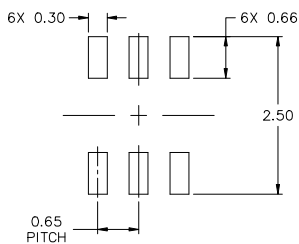
DATE 18 APR 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

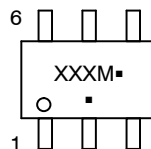


DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.00	---	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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**CASE 419B-02**  
**ISSUE Z**

DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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